

Description

This 30V 56A, N-Channel MOSFET in a PDFN5\*6 Plastic Package.

Features

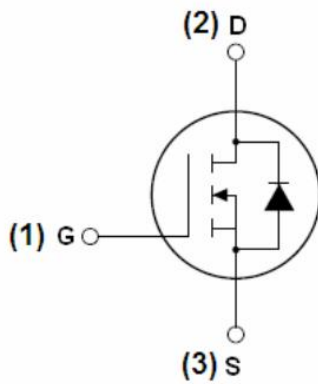
- Low  $R_{DS(on)}$  to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance
- Halogen-free Product

Applications

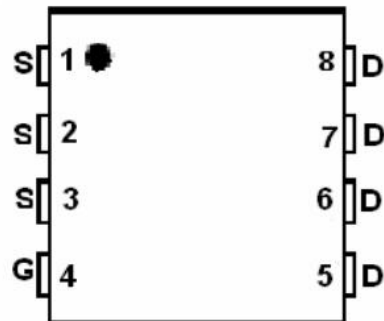
- Battery Management
- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

$V_{DSS}$	$R_{DS(on)}$ Typ	$I_D$
30V	2.9mΩ	56A

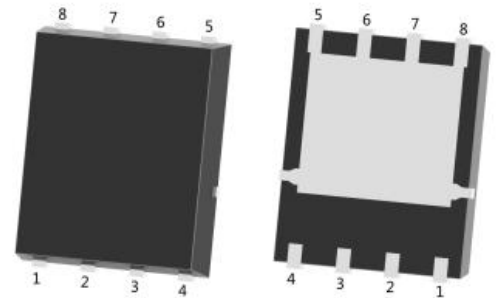
Equivalent Circuit & Pinning



Schematic diagram



Pin assignment



PDFN5X6-8L

**Absolute Maximum Ratings(Ta=25°C)**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Continuous Drain Current	$I_D$	56	A
Pulsed Drain Current	$I_{DM}$	168	A
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	33	W
Avalanche energy(L=0.5mH)	$E_{AS}$	72	mJ
Avalanche Current(L=0.5mH)	$I_{AS}$	36	A
Junction and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient	t ≤ 10s	$R_{\theta JA}$	30
	Steady-State		54
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	3.8

**Electrical Characteristics(Ta=25°C)**

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	30	31		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$			1.0	$\mu\text{A}$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 10$ 0	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=20\text{A}$		2.9	3.1	m $\Omega$
		$V_{GS}=4.5\text{V}, I_D=10\text{A}$		4.1	4.8	
Diode Forward Voltage	$V_{SD}$	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.68	1	V
Input Capacitance	$C_{iss}$	$V_{DS}=25\text{V}, V_{GS}=0\text{V}$ $f=1.0\text{MHz}$		3030		pF
Output Capacitance	$C_{oss}$			355		
Reverse Transfer Capacitance	$C_{rss}$			260		
Gate resistance	$R_g$	$V_{GS}=0\text{V}, V_{DS}=0\text{V}$ $f=1\text{MHz}$		3		$\Omega$
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10\text{V}, V_{DS}=15\text{V},$ $I_D=20\text{A}$		63		nC
Total Gate Charge	$Q_{g(4.5V)}$			29		
Gate Source Charge	$Q_{gs}$			9.0		
Gate Drain Charge	$Q_{gd}$			9.5		

## Electrical Characteristics(Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_L=0.75\Omega$ $R_{GEN}=3\Omega$		9		ns
Turn-On Rise Time	$t_r$			6		
Turn-Off Delay Time	$t_{d(off)}$			52		
Turn-Off Fall Time	$t_f$			11.5		

Electrical Characteristic Curve

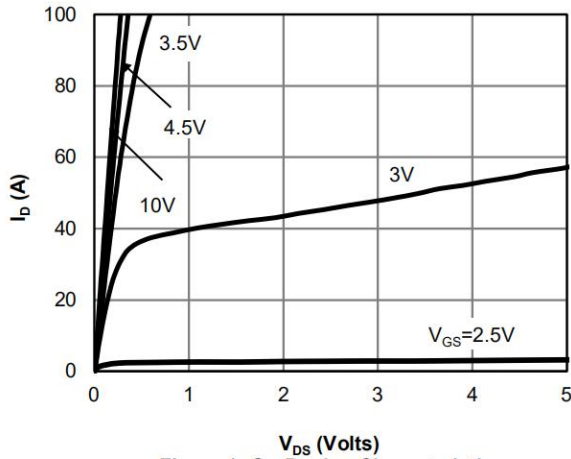


Figure 1: On-Region Characteristics

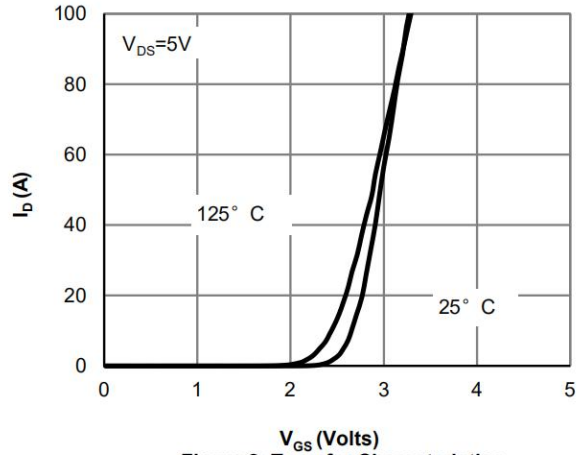


Figure 2: Transfer Characteristics

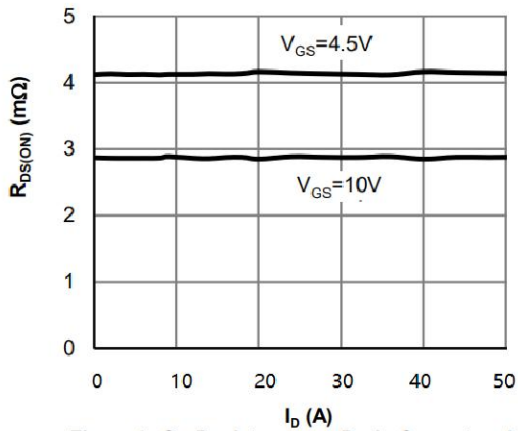


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

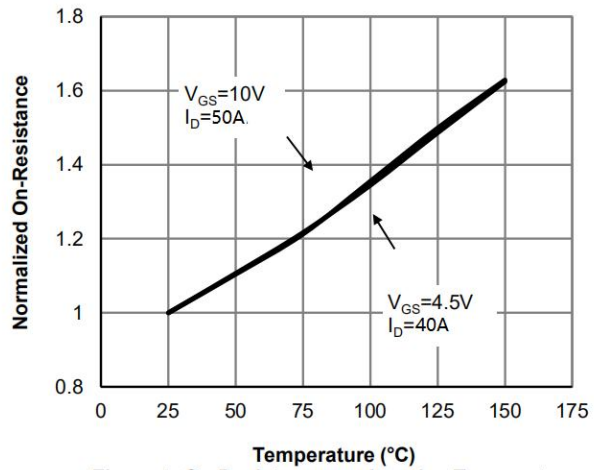


Figure 4: On-Resistance vs. Junction Temperature

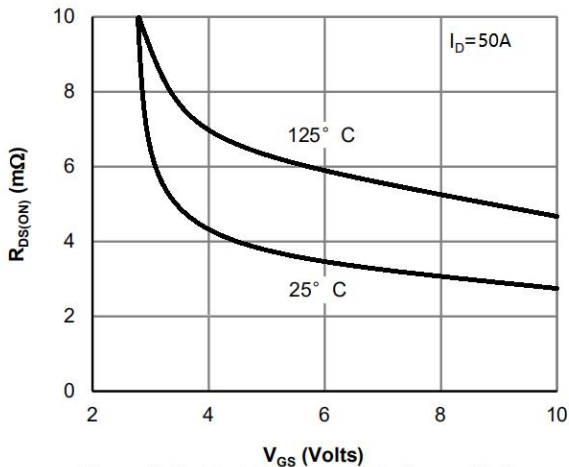


Figure 5: On-Resistance vs. Gate-Source Voltage

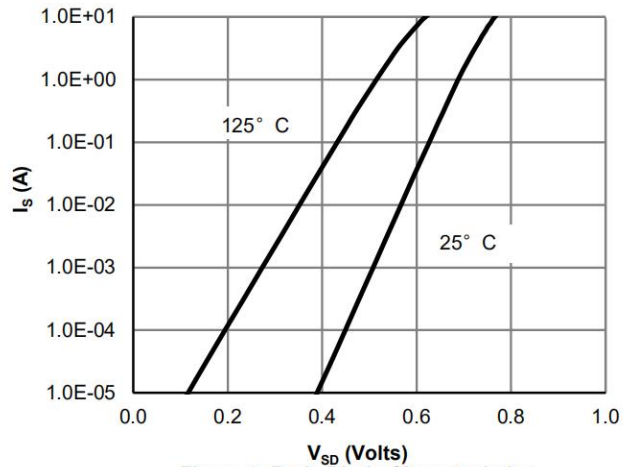


Figure 6: Body-Diode Characteristics

Electrical Characteristic Curve

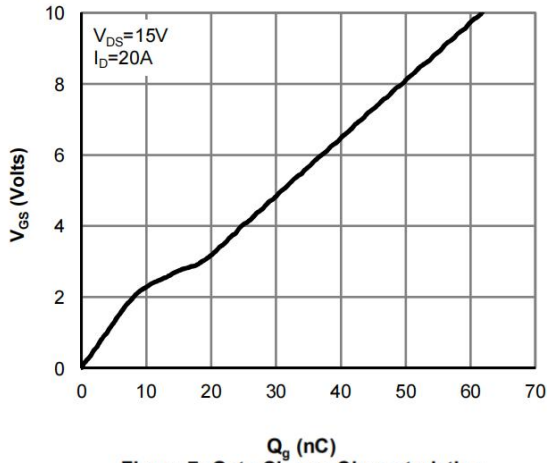


Figure 7: Gate-Charge Characteristics

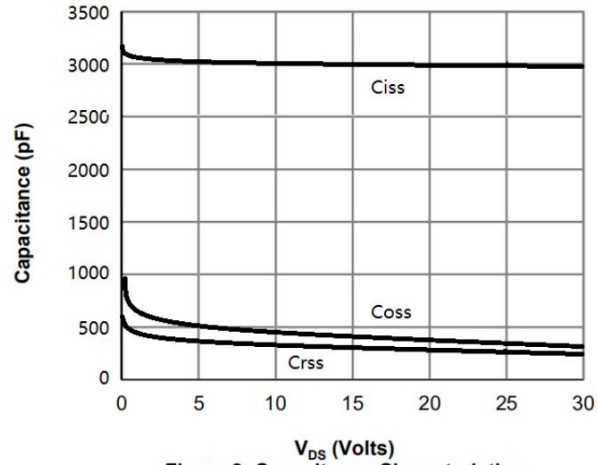


Figure 8: Capacitance Characteristics

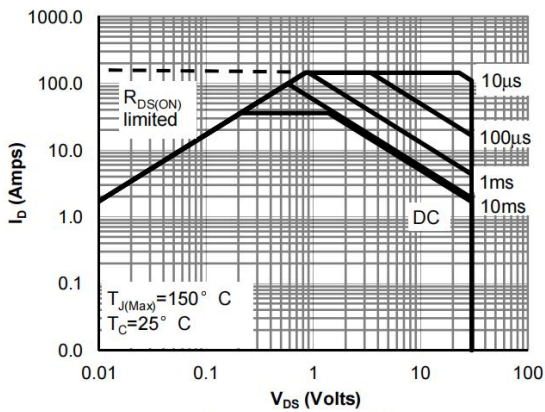


Figure 9: Maximum Forward Biased Safe Operating Area

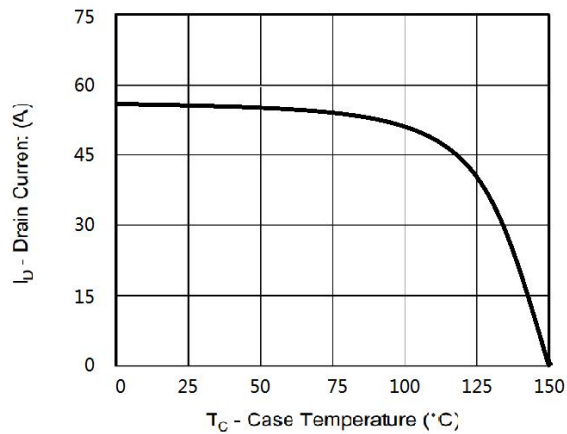


Figure 10: Maximum Continuous Drain Current vs Case Temperature

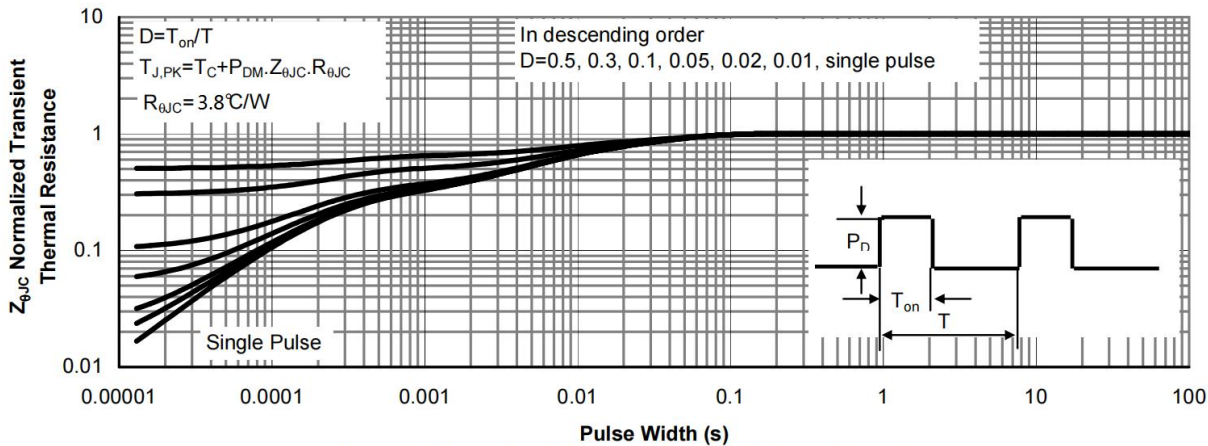
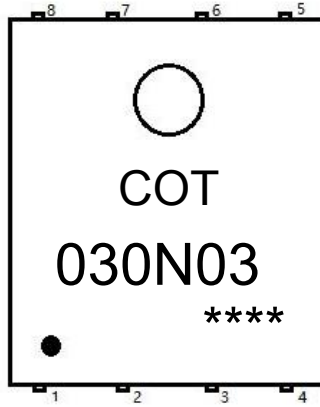


Figure 10: Normalized Maximum Transient Thermal Impedance

Marking Instructions



Note:

COT: Company Logo

030N03: Product Type.

\*\*\*\*: Lot No. Code, code change with Lot No.

Packaging SPEC.

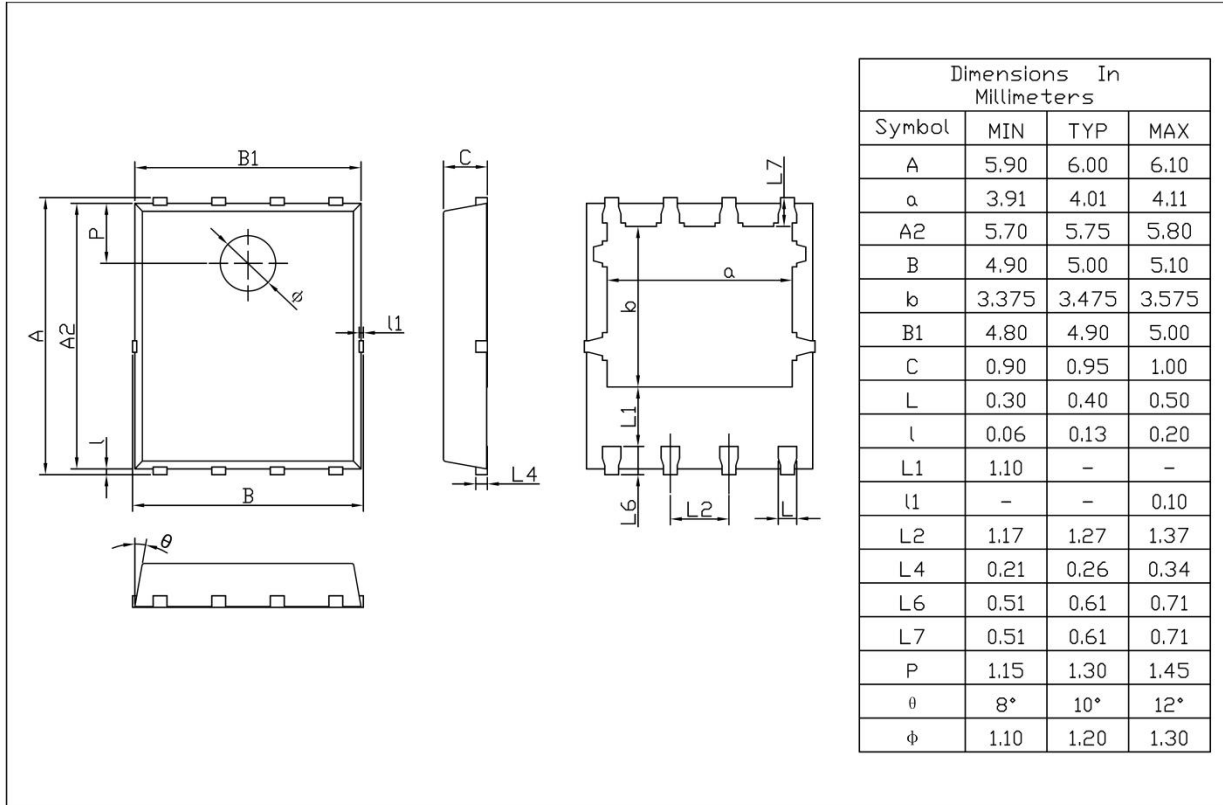
REEL INFORMATION

Package Type	Units					Dimension (unit: mm <sup>3</sup> )		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
PDFN5*6	5000	2	10000	6	60000	13" × 12	360 × 360 × 50	380 × 335 × 366

Package Outline Dimensions

PDFN5 X6

Unit:mm



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